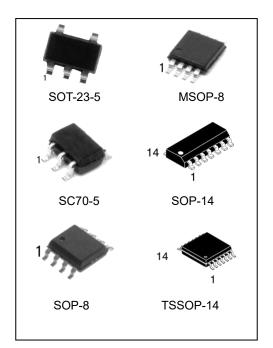


# 350KHZ Zero-Drift CMOS Rail-to-Rail IO Opamp with RF Filter

### Features

- Single-Supply Operation from +1.8V ~ +5.5V
- Rail-to-Rail Input / Output
- Gain-Bandwidth Product: 350KHz (Typ. @25°C)
- Low Input Bias Current: 20pA (Typ. @25°C)
- Low Offset Voltage: 10uV (Max. @25°C)
- Quiescent Current: 25µA per Amplifier (Typ)
- Operating Temperature: -45°C ~ +125°C
- Zero Drift: 0.05µV/°C (Typ)
- Embedded RF Anti-EMI Filter
- Small Package:

HGV8331 Available in SOT-23-5, SC70-5 and SOP-8 Packages HGV8332 Available in SOP-8, MSOP-8 Packages HGV8334 Available in SOP-14 and TSSOP-14 Packages



#### **ORDERING INFORMATION**

DEVICE	Package Type	MARKING	Packing	Packing Qty
HGV8331M5/TR	SOT-23-5	8331	REEL	3000pcs/reel
HGV8331M7/TR	SC70-5	8331	REEL	3000pcs/reel
HGV8331M/TR	SOP-8	V8331	REEL	2500pcs/reel
HGV8332M/TR	SOP-8	V8332	REEL	2500pcs/reel
HGV8332MM/TR	MSOP-8	V8332	REEL	3000pcs/reel
HGV8334M/TR	SOP-14	HGV8334	REEL	2500pcs/reel
HGV8334MT/TR	TSSOP-14	V8334	REEL	2500pcs/reel



# **General Description**

The HGV833X amplifier is single/dual/quad supply, micro-power, zero-drift CMOS operational amplifiers, the amplifiers offer bandwidth of 350 kHz, rail-to-rail inputs and outputs, and single-supply operation from 1.8V to 5.5V. HGV833X uses chopper stabilized technique to provide very low offset voltage (less than 10µV maximum) and near zero drift over temperature. Low quiescent supply current of 25µA per amplifier and very low input bias current of 20pA make the devices an ideal choice for low offset, low power consumption and high impedance applications. The HGV833X offers excellent CMRR without the crossover associated with traditional complementary input stages. This design results in superior performance for driving analog-to-digital converters (ADCs) without degradation of differential linearity.

The HGV8331 is available in SOT-23-5, SC70-5 and SOP8 packages. And the HGV8332 is available in SOP8 and MSOP8 packages. The HGV8334 Quad is available in Green SOP-14 and TSSOP-14 packages. The extended temperature range of-45°C to +125°C over all supply voltages offers additional design flexibility.

## Applications

- Transducer Application
- Temperature Measurements
- Electronics Scales
- Handheld Test Equipment
- Battery-Powered Instrumentation

# **Pin Configuration**

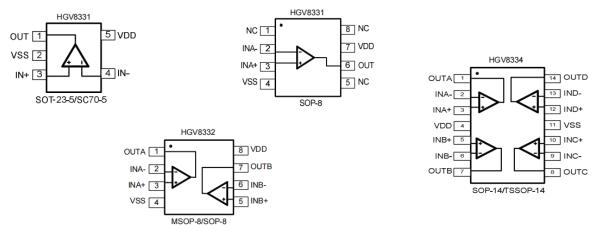


Figure 1. Pin Assignment Diagram



#### **Absolute Maximum Ratings**

Condition	Min	Мах			
Power Supply Voltage (VDD to Vss)	-0.5V	+7.5V			
Analog Input Voltage (IN+ or IN-)	Vss-0.5V	VDD+0.5V			
PDB Input Voltage	Vss-0.5V	+7V			
Operating Temperature Range	-45°C	+125°C			
Junction Temperature	+160	0°C			
Storage Temperature Range	-55°C	+150°C			
Lead Temperature (soldering, 10sec)	+245°C				
Package Thermal Resistan	ce (TA=+25℃)				
SOP-8, θJA	125°	C/W			
MSOP-8, θJA	216°	C/W			
SOT-23-5, θJA	190°	C/W			
ESD Susceptibi	lity				
НВМ	6KV				
MM	400	)V			

#### Note:

Stress greater than those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification are not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.



## **Electrical Characteristics**

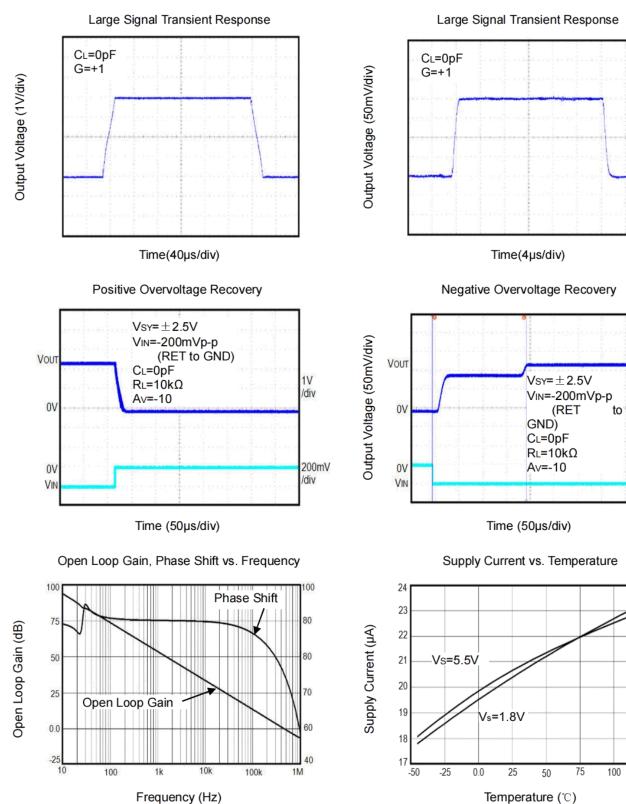
(At Vs=5V, TA = +25 $^{\circ}$ C, VCM = VS/2, RL = 10K $\Omega$ , unless otherwise noted.)

PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNITS
INPUT CHARACTERISTICS					
Input Offset Voltage (VOS)			2	10	μV
Input Bias Current (IB)			20		pА
Input Offset Current (IOS)			10		pА
Common-Mode Rejection Ratio (CMRR)	VCM = 0V to 5V		110		dB
Large Signal Voltage Gain (AVO)	$R_L = 10k\Omega$ , $V_O = 0.3V$ to 4.7V		145		dB
Input Offset Voltage Drift ( $\Delta VOS/\Delta T$ )			50		nV/℃
OUTPUT CHARACTERISTICS					
Quitout Voltage High (VQU)	RL = 100kΩ to - VS		4.998		V
Output Voltage High (VOH)	$R_L = 10k\Omega$ to - VS		4.994		V
Output Voltage Low (VOL)	$RL = 100k\Omega$ to + VS		5		mV
	$R_L = 10k\Omega$ to + VS		20		mV
Short Circuit Limit (ISC)	RL =10Ω to - VS		20		mA
Output Current (IO)			30		mA
POWER SUPPLY					
Power Supply Rejection Ratio (PSRR)	VS = 2.5V to 5.5V		115		dB
Quiescent Current (IQ)	VO = 0V, RL = 0Ω		25		μA
DYNAMIC PERFORMANCE					
Gain-Bandwidth Product (GBP)	G = +100		350		KHz
Slew Rate (SR)	RL = 10kΩ		0.2		V/µs
NOISE PERFORMANCE					
Voltage Noise (en p-p)	0Hz to 10Hz		1.1		µVP-P
Voltage Noise Density (en)	f = 1kHz		70		$nV/\sqrt{Hz}$



## **Typical Performance characteristics**

(TA=+25°C, Vs=5V, RL=10 k $\Omega$  connected to VS/2 and VOUT= VS/2, unless otherwise noted.)



125

1V

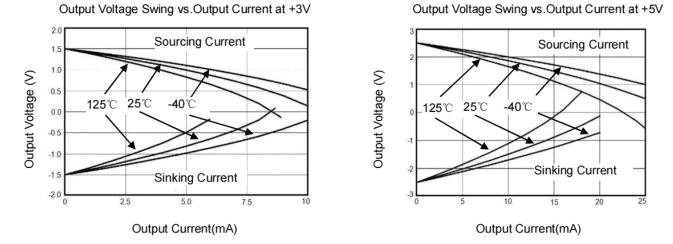
/div

200mV /div



### **Typical Performance characteristics**

(TA=+25°C, Vs=5V, RL=10 k $\Omega$  connected to VS/2 and VOUT= VS/2, unless otherwise noted.)



## **Application Note**

#### Size

HGV833X series op amps are unity-gain stable and suitable for a wide range of general-purpose applications. The small footprints of the HGV833X series packages save spaceon printed circuit boards and enable the design of smaller electronic products.

#### Power Supply Bypassing and Board Layout

HGV833X series operates from a single 1.8V to 5.5V supply or dual  $\pm 0.9V$  to  $\pm 2.75V$  supplies. For best performance, a 0.1µF ceramic capacitor should be placed close to the VDD pin in single supply operation. For dual supply operation, both VDD and VSS supplies should be bypassed to ground with separate 0.1µF ceramic capacitors.

## Low Supply Current

The low supply current (typical 25uA per channel) of HGV833X series will help to maximize battery life. They are ideal for battery powered systems

# **Operating Voltage**

HGV833X series operate under wide input supply voltage (1.8V to 5.5V). In addition, all temperature specifications apply from-45 oC to +125 oC. Most behavior remains unchanged throughout the full operating voltage range. These guarantees ensure operation throughout the single Li-lon battery lifetime

## **Rail-to-Rail Input**

The input common-mode range of HGV833X series extends 100mV beyond the supply rails (VSS-0.1V to VDD+0.1V). This is achieved by using complementary input stage. For normal operation, inputs should be limited to this range.

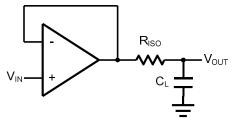
# Rail-to-Rail Output

Rail-to-Rail output swing provides maximum possible dynamic range at the output. This is particularly important when operating in low supply voltages. The output voltage of HGV833X series can typically swing to less than 5mV from supply rail in light resistive loads (>100k $\Omega$ ), and 100mV of supply rail in moderate resistive loads (10k $\Omega$ ).



## **Capacitive Load Tolerance**

The HGV833x family is optimized for bandwidth and speed, not for driving capacitive loads. Output capacitance will create a pole in the amplifier's feedback path, leading to excessive peaking and potential oscillation. If dealing with load capacitance is a requirement of the application, the two strategies to consider are (1) using a small resistor in series with the amplifier's output and the load capacitance and (2) reducing the bandwidth of the amplifier's feedback loop by increasing the overall noise gain. Figure 2. shows a unity gain follower using the series resistor strategy. The resistor isolates the output from the capacitance and, more importantly, creates a zero in the feedback path that compensates for the pole created by the output capacitance.



#### Figure 2. Indirectly Driving a Capacitive Load Using Isolation Resistor

The bigger the RISO resistor value, the more stable VOUT will be. However, if there is a resistive load RL in parallel with the capacitive load, a voltage divider (proportional to RISO/RL) is formed, this will result in a gain error.

The circuit in Figure 3 is an improvement to the one in Figure 2. RF provides the DC accuracy by feed-forward the VIN to RL. CFand RISO serve to counteract the loss of phase margin by feeding the high frequency component of the output signal back to the amplifier's inverting input, thereby preserving the phase margin in the overall feedback loop. Capacitive drive can be increased by increasing the value of CF. This in turn will slow down the pulse response.

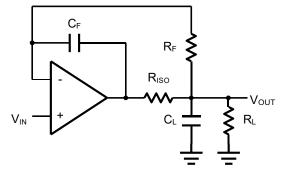


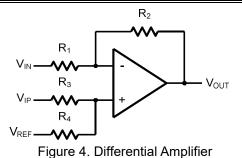
Figure 3. Indirectly Driving a Capacitive Load with DC Accuracy

## **Typical Application Circuits**

#### **Differential amplifier**

The differential amplifier allows the subtraction of two input voltages or cancellation of a signal common the two inputs. It is useful as a computational amplifier in making a differential to single-end conversion or in rejecting a common mode signal. Figure 4. shown the differential amplifier using HGV833X.





$$V_{\text{OUT}} = \left(\frac{R_1 + R_2}{R_2 + R_4}\right) \frac{R_4}{R_1} V_{\text{IN}} - \frac{R_2}{R_1} V_{\text{IP}} + \left(\frac{R_1 + R_2}{R_2 + R_4}\right) \frac{R_2}{R_1} V_{\text{REF}}$$

If the resistor ratios are equal (i.e.  $R_1=R_3$  and  $R_2=R_4$ ), then

$$V_{\rm OUT} = \frac{R_2}{R_1} (V_{\rm IP} - V_{\rm IN}) + V_{\rm REF}$$

#### Low Pass Active Filter

The low pass active filter is shown in Figure 5. The DC gain is defined by -R2/R1. The filter has a -20dB/decade roll-off after its corner frequency  $fC=1/(2\pi R3C1)$ .

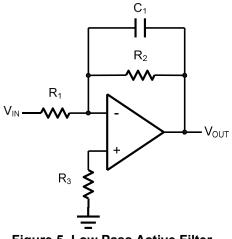
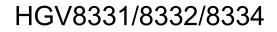


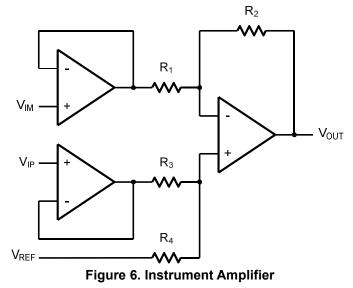
Figure 5. Low Pass Active Filter

#### **Instrumentation Amplifier**

The triple HGV833X can be used to build a three-op-amp instrumentation amplifier as shown in Figure 6. The amplifier in Figure 6 is a high input impedance differential amplifier with gain of R2/R1. The two differential voltage followers assure the high input impedance of the amplifier.



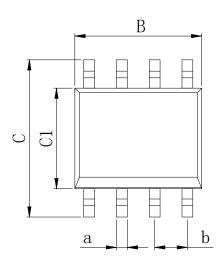


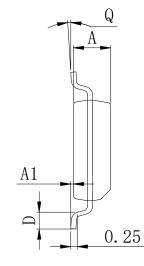




# **Physical Dimensions**

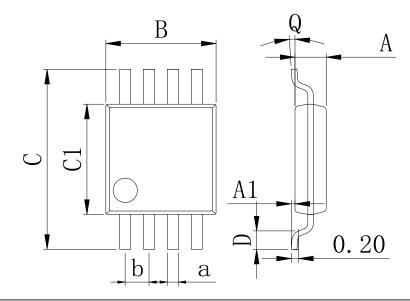
SOP-8





Dimensions In Millimeters(SOP-8)									
Symbol:	A	A1	В	С	C1	D	Q	а	b
Min:	1.35	0.05	4.90	5.80	3.80	0.40	0°	0.35	1.27 BSC
Max:	1.55	0.20	5.10	6.20	4.00	0.80	8°	0.45	1.27 630

#### MSOP-8



Dimensions In Millimeters(MSOP-8)									
Symbol:	A	A1	В	С	C1	D	Q	а	b
Min:	0.80	0.05	2.90	4.75	2.90	0.35	0°	0.25	0.65 BSC
Max:	0.90	0.20	3.10	5.05	3.10	0.75	8°	0.35	0.00 050

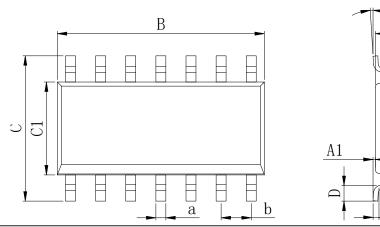


Q

0.25

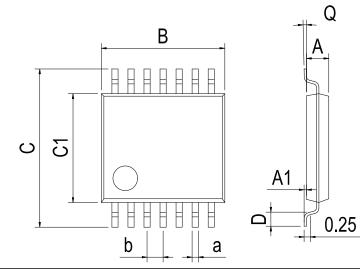
# **Physical Dimensions**

SOP-14



Dimensions In Millimeters(SOP-14)									
Symbol:	A	A1	В	С	C1	D	Q	а	b
Min:	1.35	0.05	8.55	5.80	3.80	0.40	0°	0.35	1.27 BSC
Max:	1.55	0.20	8.75	6.20	4.00	0.80	8°	0.45	1.27 650

TSSOP-14

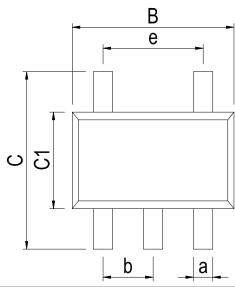


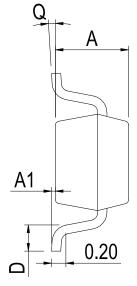
Dimensions In Millimeters(TSSOP-14)									
Symbol:	А	A1	В	С	C1	D	Q	а	b
Min:	0.85	0.05	4.90	6.20	4.30	0.40	0°	0.20	0.65 BSC
Max:	0.95	0.20	5.10	6.60	4.50	0.80	8°	0.25	0.05 BSC



# **Physical Dimensions**

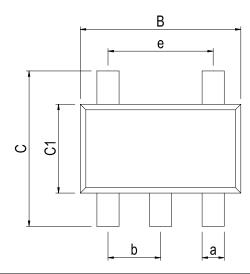
SOT-23-5

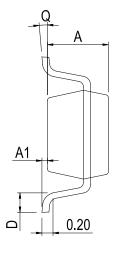




Dimensions In Millimeters(SOT-23-5)										
Symbol:	A	A1	В	С	C1	D	Q	а	b	е
Min:	1.05	0.00	2.82	2.65	1.50	0.30	0°	0.30	0.95 BSC	1.90 BSC
Max:	1.15	0.15	3.02	2.95	1.70	0.60	8°	0.40	0.95 650	

SC70-5





Dimensions In Millimeters(SC70-5)										
Symbol:	A	A1	В	С	C1	D	Q	а	b	е
Min:	0.90	0.00	2.00	2.15	1.15	0.26	0°	0.15	0.65	1.30 BSC
Max:	1.00	0.15	2.20	2.45	1.35	0.46	8°	0.35	BSC	1.30 630



# **Revision History**

DATE	REVISION	PAGE
2018-8-9	New	1-14
2023-10-31	Update encapsulation type, Update Lead Temperature, Update SC70-5 Physical	1, 3, 12
2023-10-31	Dimensions	1, 3, 12





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